

Silicon NPN Power Transistors

2SC1027

DESCRIPTION

- With TO-3 package
- High power dissipation
- Low collector saturation voltage

APPLICATIONS

- Switching regulators
- DC-DC convertor
- General purpose power amplifiers

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

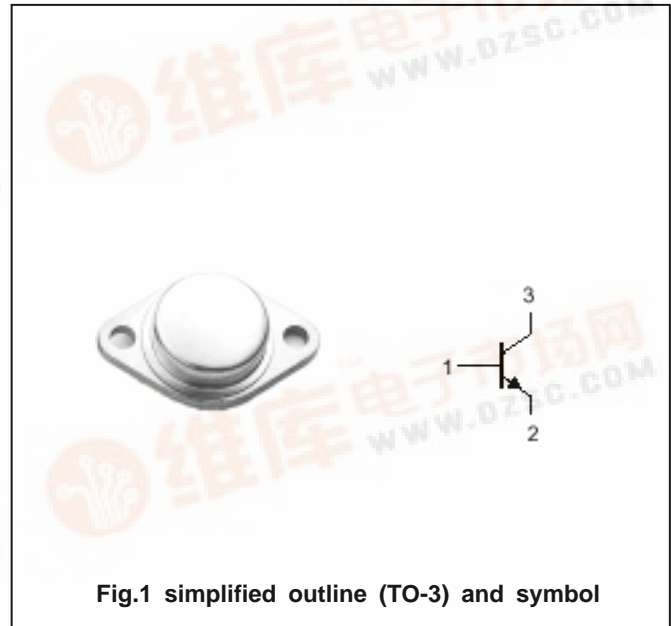


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	250	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
P _C	Collector power dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	80			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	250			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =0.5A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A ; I _B =0.5A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =250V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =2V	10			

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PACKAGE OUTLINE

